

DSS5140U

40V PNP LOW SATURATION TRANSISTOR IN SOT323

Features

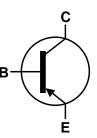
- BV_{CEO} > -40V
- I_C = -1A Continuous Collector Current
- I_{CM} = -2A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -500mV @ I_C = -1A
- Ultra-Small Surface Mount Package
- Complementary NPN Type: DSS4140U
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

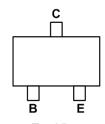
- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated leads. Solderable per MIL-STD-202, Method 208 <a>®3
- Weight: 0.006 grams (Approximate)







Device Symbol



Top View Pin-Out

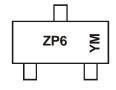
Ordering Information (Note 4)

Device	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per reel
DSS5140U-7	AEC-Q101	ZP6	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZP6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	201	0	2011	2012	2013	2014	2015	2016	6 20	17 2	2018	2019	2020
Code	Х		Υ	Z	Α	В	С	D	Е		F	G	Н
Mont	h	Jan	n Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code)	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current - Continuous	Ic	-1	Α
Peak Pulse Collector Current	I _{CM}	-2	Α
Peak Base Current	I _{BM}	-1	Α

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	C-	400	mW	
Power Dissipation	(Note 6)	P _D	500	IIIVV	
Thormal Pagistance, Junation to Ambient	(Note 5)	0	313	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	250	C/VV	
Thermal Resistance, Junction to Leads	(Note 7)	$R_{ heta JL}$	350	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

^{5.} For a device mounted with collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

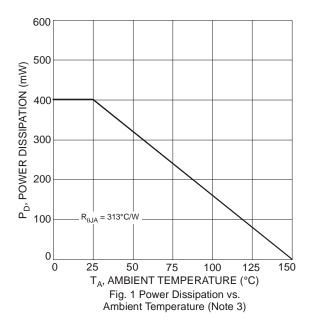
6. Same as Note 5, except the collector lead is on a 25mm x 25mm loz copper.

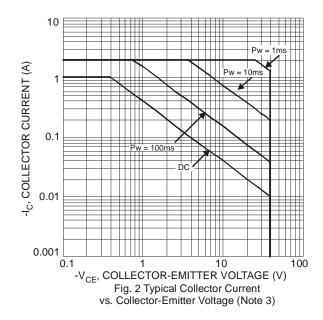
7. Thermal resistance from junction to solder-point (at the end of the leads).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





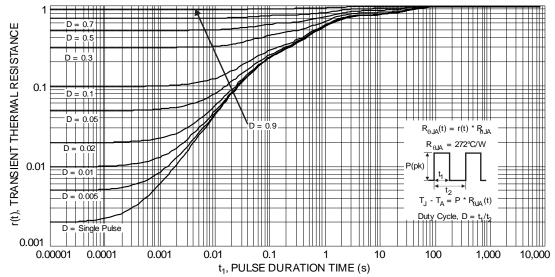


Fig. 3 Transient Thermal Response (Note 3)



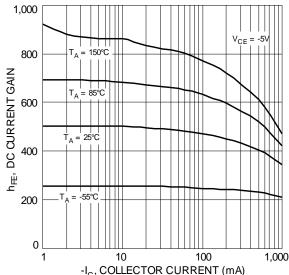
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

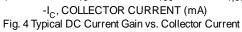
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS	OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-40	_		V	$I_C = -100\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage (Note 9)	BV_CEO	-40	_	_	V	$I_C = -10 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	_		V	$I_E = -100\mu A, I_C = 0$	
Collector Cutoff Current	I _{CBO}	_	_	-100	nA	$V_{CB} = -40V, I_{E} = 0$	
	1CBO			-50	μA	$V_{CB} = -40V, I_E = 0, T_J = +150^{\circ}C$	
Collector Cutoff Current	I _{CES}	_	_	-100	nA	$V_{CE} = -40V, V_{BE} = 0$	
Emitter Cutoff Current	I _{EBO}	_	_	-100	nA	$V_{EB} = -5V, I_C = 0$	
ON CHARACTERISTICS (Note 9)							
		300	_	_		$V_{CE} = -5V$, $I_C = -1mA$	
DC Current Gain	h _{FE}	300	_	800	_	$V_{CE} = -5V, I_{C} = -100mA$	
20 04.110.11 04.11.	''FE	250	_	_		$V_{CE} = -5V, I_{C} = -500mA$	
		160	_	_		$V_{CE} = -5V$, $I_C = 1A$	
	V _{CE(SAT)}	_	_	-200		$I_C = -100 \text{mA}, I_B = -1 \text{mA}$	
Collector-Emitter Saturation Voltage		_	_	-250	mV	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$	
		_	_	-500		$I_C = -1A$, $I_B = -100mA$	
Collector-Emitter Saturation Resistance	R _{CE(SAT)}	_	_	500	mΩ	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$	
Base-Emitter Saturation Voltage	V _{BE(SAT)}		_	-1.1	V	$I_C = -1A$, $I_B = -50mA$	
Base-Emitter Turn On Voltage	V _{BE(ON)}	_	_	-1	V	$V_{CE} = -5V, I_{C} = -1A$	
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C_{obo}		13		pF	V _{CB} = -10V, f = 1.0MHz	
Current Gain-Bandwidth Product	f_T	150	_	_	MHz	$V_{CE} = -10V$, $I_{C} = -50mA$, $f = 100MHz$	
SWITCHING CHARACTERISTICS							
Turn-On Time	t _{on}		60	_	ns		
Delay Time	t _d		25	_	ns		
Rise Time	t _r	_	35		ns	V _{CC} = -10V	
Turn-Off Time	t _{off}	_	250	_	ns	$I_C = -0.5A$, $I_{B1} = -I_{B2} = -25mA$	
Storage Time	ts	_	220	_	ns		
Fall Time	t _f		30	_	ns		

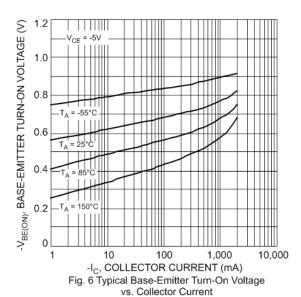
Note: 9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

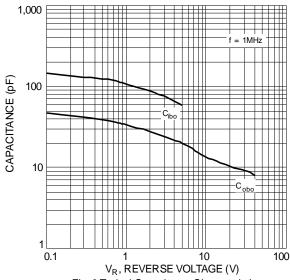


Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)









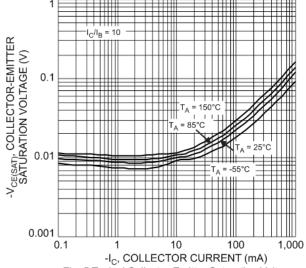


Fig. 5 Typical Collector-Emitter Saturation Voltage vs. Collector Current

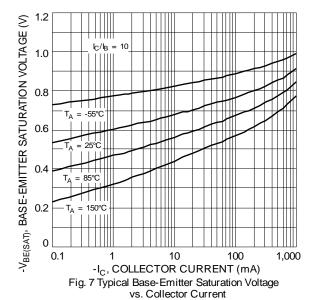
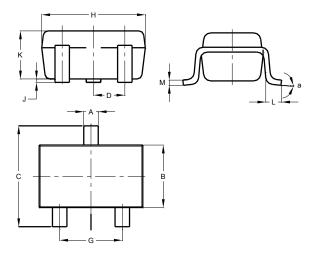


Fig. 8 Typical Capacitance Characteristics



Package Outline Dimensions

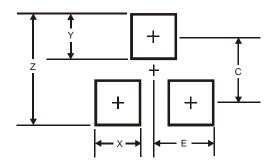
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT323						
Dim	Min	Max	Тур				
Α	0.25	0.40	0.30				
В	1.15	1.35	1.30				
С	2.00	2.20	2.10				
D	0.	.650 BS	C				
F	0.375	0.475	0.425				
G	1.20	1.40	1.30				
Н	1.80	2.20	2.15				
J	0.00	0.10	0.05				
K	0.90	1.00	0.95				
L	0.25	0.40	0.30				
М	0.10	0.18	0.11				
а	8°C						
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	SOT323
Z	2.8
Х	0.7
Υ	0.9
С	1.9
E	1.0



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